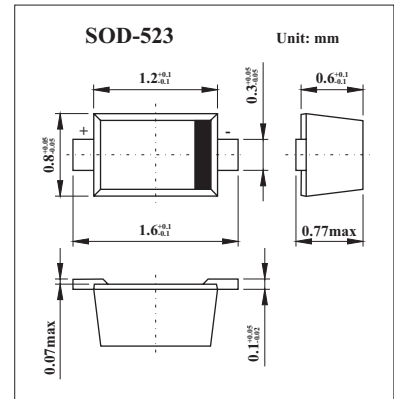


Silicon Epitaxial Trench Pin Diode

HVC135



■ Features

- Adopting the trench structure improves low capacitance. ($C=0.6\text{pF max}$)
- Low forward resistance. ($r_f=2.0\ \Omega\ \text{max}$)
- Low operation current.

■ Absolute Maximum Ratings $T_a = 25\ ^\circ\text{C}$

Parameter	Symbol	Value	Unit
Peak reverse voltage	V_{RM}	65	V
Reverse voltage	V_R	60	V
Forward current	I_F	100	mA
Power dissipation	P_d	150	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25\ ^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current	I_R	$V_R = 60\ \text{V}$			0.1	μA
Reverse voltage	V_F	$I_F = 2\ \text{mA}$			0.9	V
Capacitance	C	$V_R = 1\ \text{V}, f = 1\ \text{MHz}$			0.6	pF
Forward resistance	r_f	$I_F = 2\ \text{mA}, f = 100\ \text{MHz}$			2.0	Ω
ESD-Capability *1		$C = 200\text{pF}$, Both forward and reverse direction 1 pulse	100			V

Note

1. Failure criterion ; $I_R > 100\ \text{nA}$ at $V_R = 60\ \text{V}$.

■ Marking

Marking	P5
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